L Number	Hits	Search Text	DB	Time stamp
1	2	438/197.ccls. and "stack structure" and photoresist and teos	USPAT	2003/07/24 11:58
-	387	438/197.ccls.	USPAT	2003/07/16 11:50
-	378	438/197.ccls. and substrate	USPAT	2003/07/16 11:58
-	89	438/197.ccls. and substrate and "conductive layer"	USPAT	2003/07/16 11:51
-	39	438/197.ccls. and substrate and "conductive layer" and "dielectric layer"	USPAT	2003/07/16 11:51
-	0	438/197.ccls. and substrate and "conductive layer" and "dielectric layer" and "buried drain"	USPAT	2003/07/16 11:51
-	37	438/197.ccls. and substrate and "conductive layer" and "dielectric layer" and "drain"	USPAT	2003/07/16 11:52
-	10	438/197.ccls. and substrate and "conductive layer" and "dielectric layer" and "drain" and "insulating layer"	USPAT	2003/07/16 11:52
-	3	438/197.ccls. and substrate and "conductive layer" and "dielectric layer" and "drain" and "insulating layer" and "silicon layer"	USPAT	2003/07/16 11:53
-	0	438/197.ccls. and substrate and "conductive layer" and "dielectric layer" and "drain" and "insulating layer" and "silicon layer" and cap	USPAT	2003/07/16 11:53
-	2	438/197.ccls. and substrate and "conductive layer" and "dielectric layer" and "drain" and "insulating layer" and "silicon layer" and nitride	USPAT	2003/07/16 11:53
-	2	438/197.ccls. and substrate and "conductive layer" and "dielectric layer" and "drain" and "insulating layer" and "silicon layer" and nitride and gate	USPAT	2003/07/16 11:53
-	6	438/197.ccls. and "non volatile memory"	USPAT	2003/07/16 11:59
-	6	438/197.ccls. and "non volatile memory" and substrate	USPAT	2003/07/16 11:59
-	6	438/197.ccls. and "non volatile memory" and substrate and conductive	USPAT	2003/07/16 12:05
-	2	438/197.ccls. and "non volatile memory" and substrate and conductive and dielectric	USPAT	2003/07/16 12:09
-	0	438/197.ccls. and "strip stack"	USPAT	2003/07/16 12:09
-	83	438/197.ccls. and "stack"	USPAT	2003/07/16 12:09
-	6	438/197.ccls. and "stack structure"	USPAT	2003/07/17 10:42
-	6	438/197.ccls. and "stack structure" and semiconductor	USPAT	2003/07/16 12:10
-	6	438/197.ccls. and "stack structure" and substrate	USPAT	2003/07/16 12:10
-	6	438/197.ccls. and "stack structure" and substrate and gate	USPAT	2003/07/16 12:10
-	4	438/197.ccls. and "stack structure" and substrate and gate and dielectric	USPAT	2003/07/16 12:10
-	0	438/197.ccls. and "stack structure" and substrate and gate and dielectric and buri$4	USPAT	2003/07/16 12:11
-	4	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain	USPAT	2003/07/16 12:11
-	4	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat$4	USPAT	2003/07/16 12:11
-	4	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat$4 and silicon	USPAT	2003/07/16 12:11
-	2	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat$4 and silicon and cap	USPAT	2003/07/16 12:12
-	1	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat$4 and silicon and cap and line$4	USPAT	2003/07/16 12:12
-	1	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat$4 and silicon and cap and line$4 and salicide	USPAT	2003/07/16 12:13

-	1	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat$4 and silicon and cap and line$4 and salicide and metal	USPAT	2003/07/17 10:42
-	4	438/197.ccls. and "stack structure" and photoresist	USPAT	2003/07/24 11:58
-	1	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat$4 and silicon and cap and line$4 and salicide and metal and photoresist	USPAT	2003/07/17 10:43